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(54) **MEMORY DEVICE AND MANUFACTURING METHOD THEREOF**

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(57) **ABSTRACT**

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The invention provides a memory and a forming method thereof. By connecting two node contact parts filled in two node contact windows at the edge and adjacent to each other, a large-sized combined contact can be formed, so that when preparing the node contact parts, the morphology of the combined contact at the edge position can be effectively ensured, and under the blocking protection of the combined contact with a large width, the rest of the node contact parts can be prevented from being greatly eroded, and the morphology accuracy of the independently arranged node contact parts can be improved, thereby being beneficial to improving the device performance of the formed memory.

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Related U.S. Application Data

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(30) **Foreign Application Priority Data**

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